

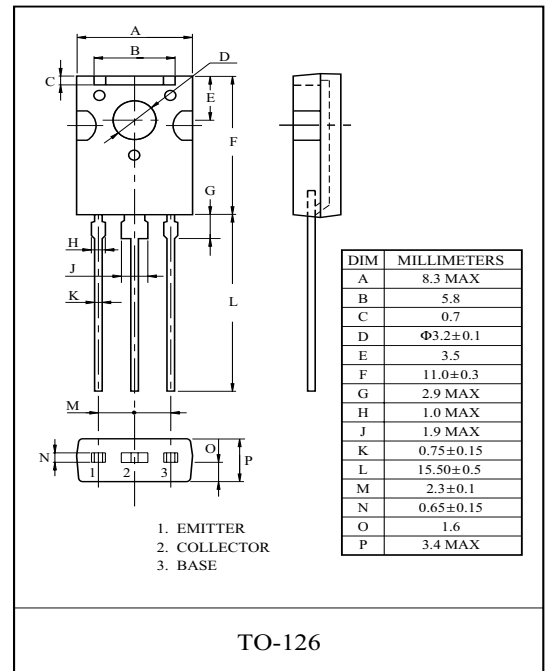
SWITCHING REGULATOR APPLICATION.
HIGH VOLTAGE AND HIGH SPEED
SWITCHING APPLICATION.

FEATURES

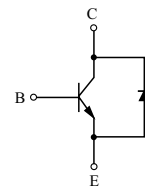
- Built-in Free Wheeling Diode
- Suitable for Electronic Ballast Application

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	700	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	9	V
Collector Current	DC	I_C	4	A
	Pulse	I_{CP}	8	
Base Current		I_B	2	A
Collector Power Dissipation (Tc=25 °C)		P_C	30	W
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	



Equivalent Circuit

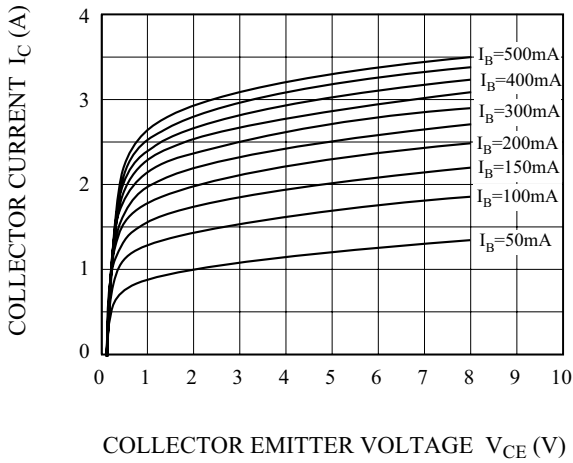


ELECTRICAL CHARACTERISTICS (Ta=25 °C)

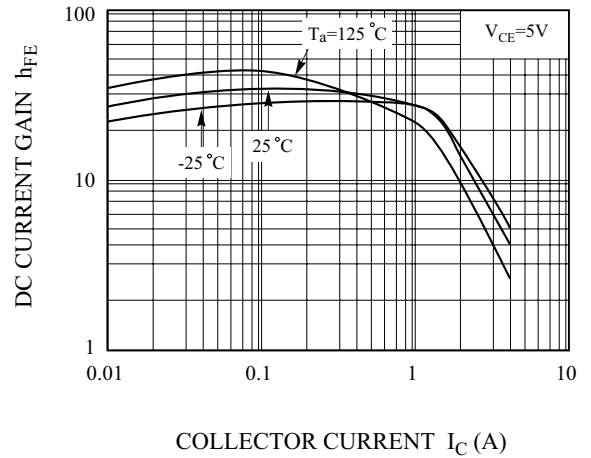
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CEO}	$V_{CE}=400V$	-	-	250	μA
Collector Cut-off Current	I_{CES}	$V_{CE}=700V, V_{EB}=0V$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=9V$	-	-	100	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=5V, I_C=10mA$	10	-	-	-
	$h_{FE}(2)$	$V_{CE}=5V, I_C=1A$	20	-	40	-
	$h_{FE}(3)$	$V_{CE}=5V, I_C=2A$	8	-	40	-
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}(1)$	$I_C=0.5A, I_B=0.1A$	-	-	0.7	V
	$V_{CE(SAT)}(2)$	$I_C=1A, I_B=0.2A$	-	-	1.0	V
	$V_{CE(SAT)}(3)$	$I_C=2.5A, I_B=0.5A$	-	-	1.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}(1)$	$I_C=0.5A, I_B=0.1A$	-	-	1.1	V
	$V_{BE(SAT)}(2)$	$I_C=1A, I_B=0.2A$	-	-	1.2	V
	$V_{BE(SAT)}(3)$	$I_C=2.5A, I_B=0.5A$	-	-	1.3	V
Internal Diode Forward Voltage Drop	V_F	$I_F=2A$	-	-	2.5	V
Resistive Load Switching						
Storage Time	t_{stg}	$V_{CC}=200V, I_C=2A,$	-	-	2.9	μS
Fall Time	t_f	$I_{B1}=I_{B2}=0.4A, T_P=30 \mu S$	-	0.2	-	μS
Inductive Load Switching						
Storage Time	t_{stg}	$V_{CC}=200V, I_C=2A, I_{B1}=0.4A,$	-	0.6	-	μS
Fall Time	t_f	$V_{BE(off)}=-5V, L=30 \mu H$	-	0.1	-	μS

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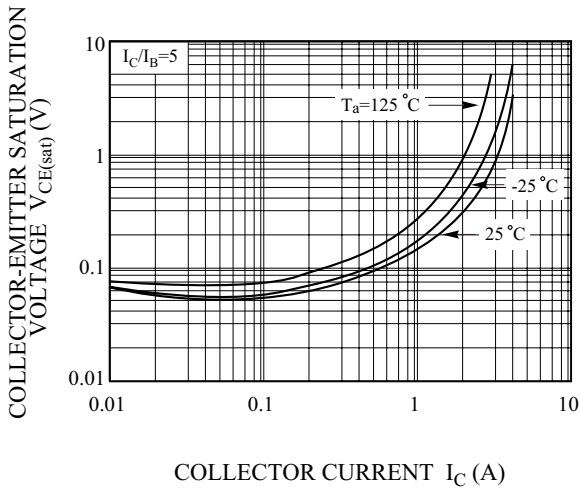
$I_C - V_{CE}$



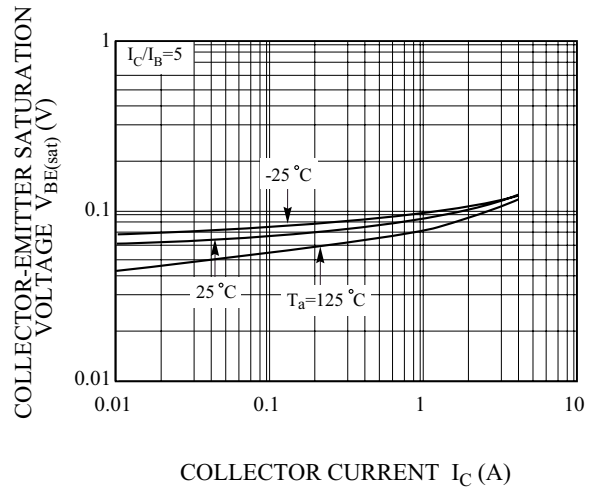
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$V_{BE(sat)} - I_C$



SAFE OPERATING AREA

